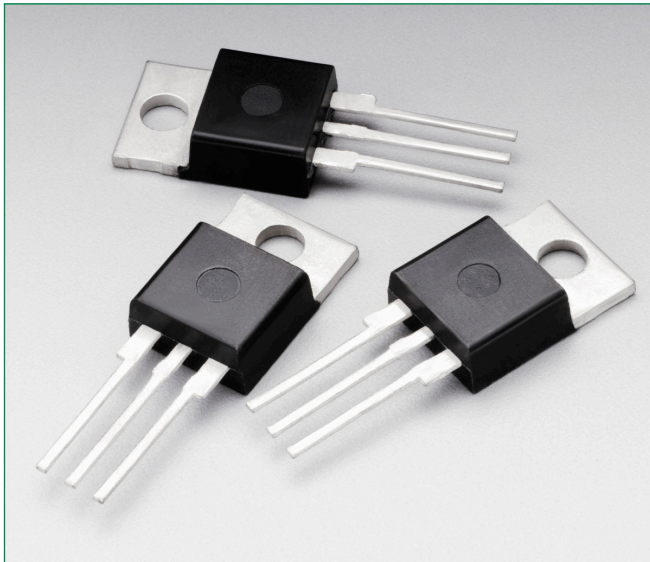


2N6394



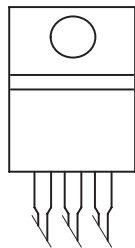
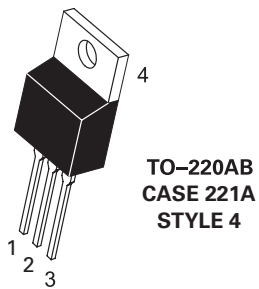
Description

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supplies.

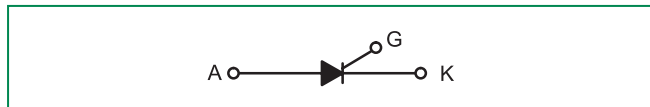
Features

- Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in all Four Quadrants
- For 400 Hz Operation, Consult Factory
- 8.0 A Devices Available as 2N6344 thru 2N6349
- Pb-Free Package is Available

Pin Out



Functional Diagram



Additional Information



[Datasheet](#)



[Resources](#)



[Samples](#)

Maximum Ratings † ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) ($T_J = -40$ to 110°C , Sine Wave, 50 to 60 Hz, Gate Open)	V_{DRM} V_{RRM}	50 100 400 800	V
On-State RMS Current (180° Conduction Angles; $T_C = 90^\circ\text{C}$)	$I_{\text{T (RMS)}}$	12	A
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, $T_J = 90^\circ\text{C}$)	I_{TSM}	100	A
Circuit Fusing Considerations ($t = 8.3$ ms)	I_{2t}	40	A ² s
Forward Peak Gate Power (Pulse Width ≤ 1.0 μs , $T_C = 90^\circ\text{C}$)	P_{GM}	20	W
Forward Average Gate Power ($t = 8.3$ ms, $T_C = 90^\circ\text{C}$)	$P_{\text{G(AV)}}$	0.5	W
Forward Peak Gate Current (Pulse Width ≤ 1.0 μs , $T_C = 90^\circ\text{C}$)	I_{GM}	2.0	A
Operating Junction Temperature Range	T_J	-40 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +125	$^\circ\text{C}$

† Indicates JEDEC Registered Data

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Maximum Ratings † ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Thermal Resistance, Junction to Case	R_{8JC}	2.0	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	$^\circ\text{C}$

† Indicates JEDEC Registered Data.

Electrical Characteristics - OFF ($T_c = 25^\circ\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
†Peak Repetitive Blocking Current ($V_{AK} = V_{DRM} = V_{RRM}$; Gate Open)	$T_J = 25^\circ\text{C}$ I_{DRM}	-	-	1.0	μA
	$T_J = 125^\circ\text{C}$ I_{RRM}	-	-	2.0	mA

Electrical Characteristics - ON ($T_c = 25^\circ\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
†Peak Forward On-State Voltage (Note 2) ($I_{TM} = 24\text{ A Peak}$)	V_{TM}	-	1.7	2.2	V
†Gate Trigger Voltage (Continuous DC), All Quadrants (Continuous dc) ($V_D = 12\text{ Vdc}$, $R_L = 100\text{ Ohms}$)	I_{GT}	-	5.0	30	mA
†Gate Trigger Voltage (Continuous dc) ($V_D = 12\text{ Vdc}$, $R_L = 100\text{ Ohms}$)	V_{GT}	-	0.7	1.5	V
Gate Non-Trigger Voltage ($V_D = 12\text{ Vdc}$, $R_L = 100\text{ Ohms}$, $T_J = 125^\circ\text{C}$)	V_{GD}	0.2	-	-	V
†Holding Current ($V_D = 12\text{ Vdc}$, Initiating Current = 200 mA, Gate Open)	I_H	-	6.0	50	mA
Turn-On Time ($I_{TM} = 12\text{ A}$, $I_{GT} = 40\text{ mAdc}$, $V_D = \text{Rated } V_{DRM}$)	t_{gt}	-	1.0	2.0	μs
Turn-Off Time ($V_D = \text{Rated } V_{DRM}$) ($I_{TM} = 12\text{ A}$, $I_R = 12\text{ A}$) ($I_{TM} = 12\text{ A}$, $I_R = 12\text{ A}$, $T_J = 125^\circ\text{C}$)	t_q	-	-	15	μs
		-	-	35	

†Indicates JEDEC Registered Data

2. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.

Dynamic Characteristics

Characteristic	Symbol	Min	Typ	Max	Unit
Critical Rate-of-Rise of Off-State Voltage Exponential ($V_D = \text{Rated } V_{DRM}$, $T_J = 125^\circ\text{C}$)	$dv/dt(c)$	-	50	-	$\text{V}/\mu\text{s}$

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current

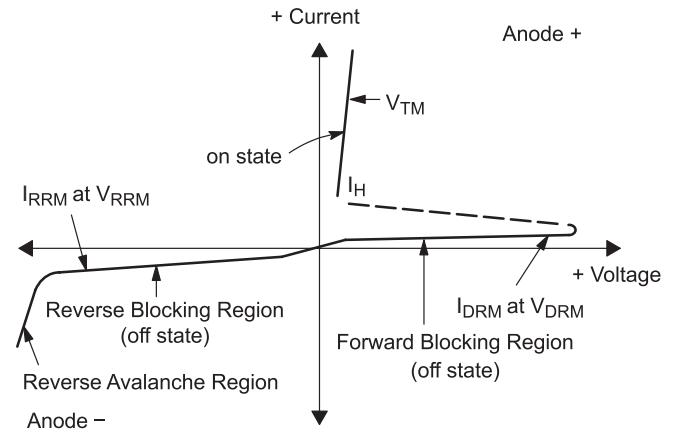


Figure 1. Current Derating

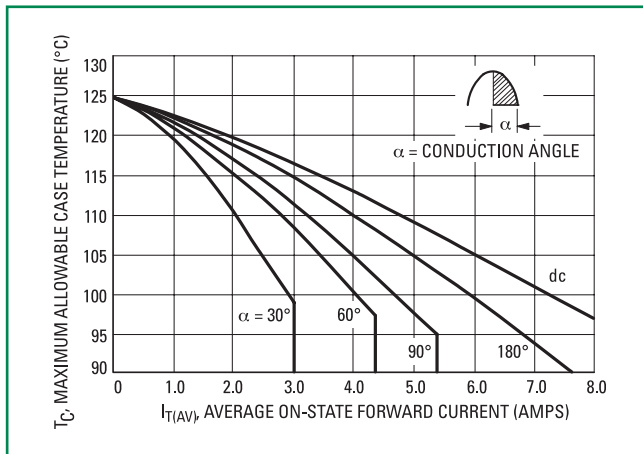


Figure 2. Maximum On-State Characteristics

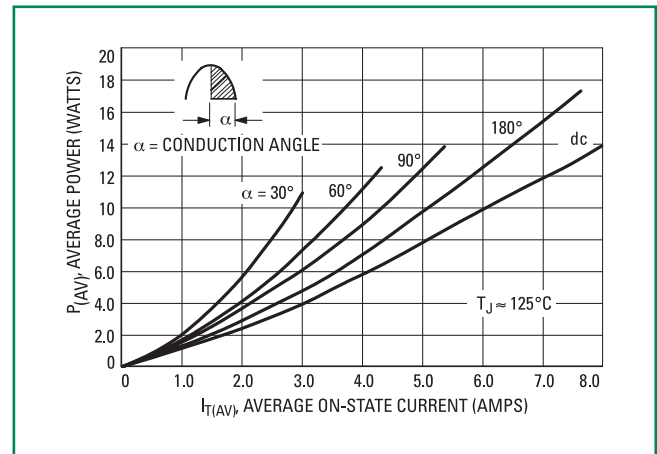


Figure 3. On-State Characteristics

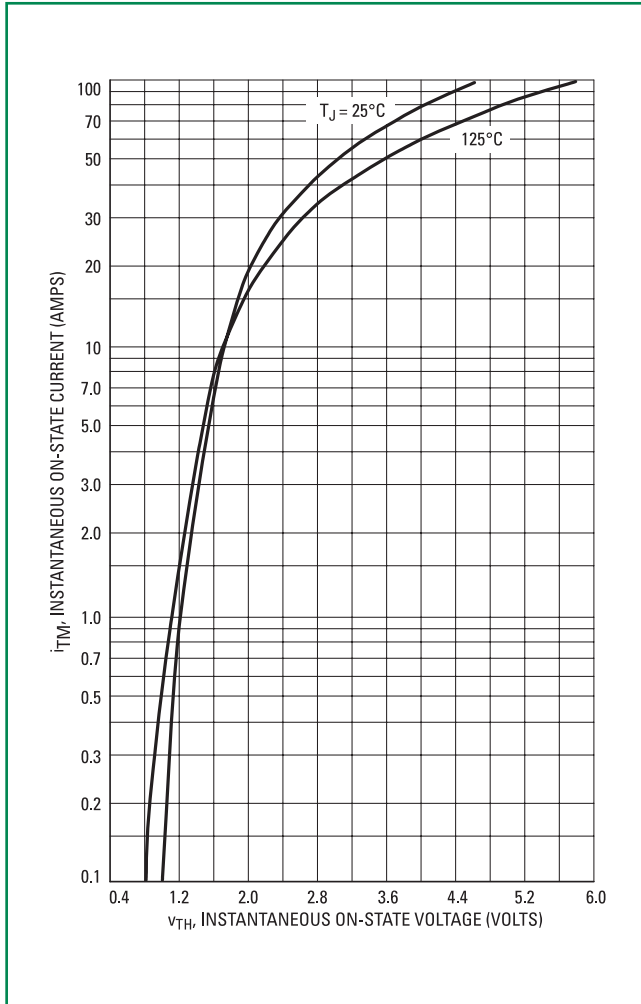


Figure 4. Maximum Non-Repetitive Surge Current

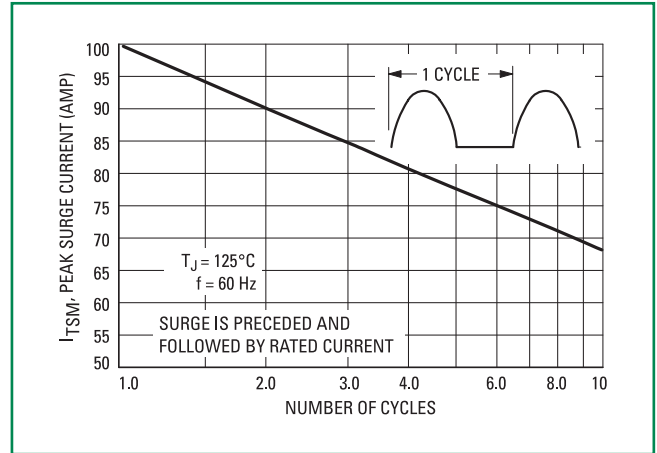
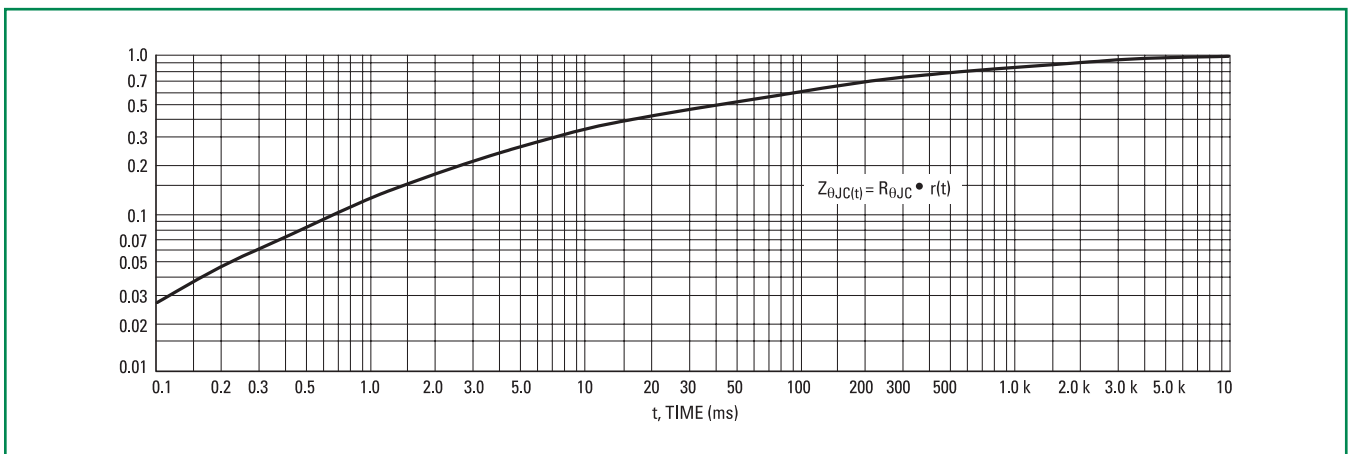


Figure 5. Typical Thermal Response



Typical Characteristics

Figure 6. Typical Gate Trigger Current vs. Pulse Width

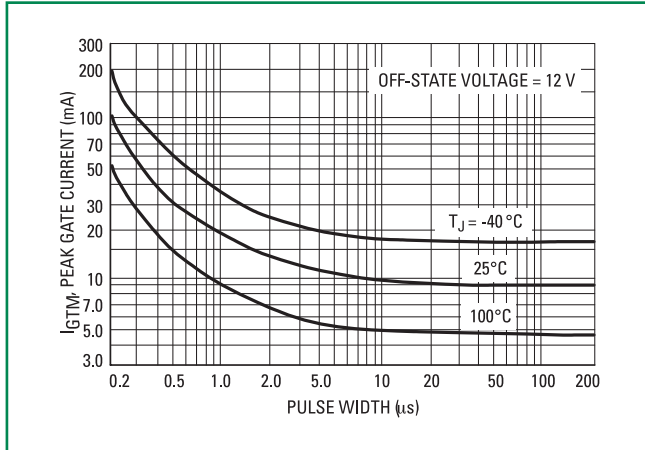


Figure 7. Typical Gate Trigger Current vs. Temperature

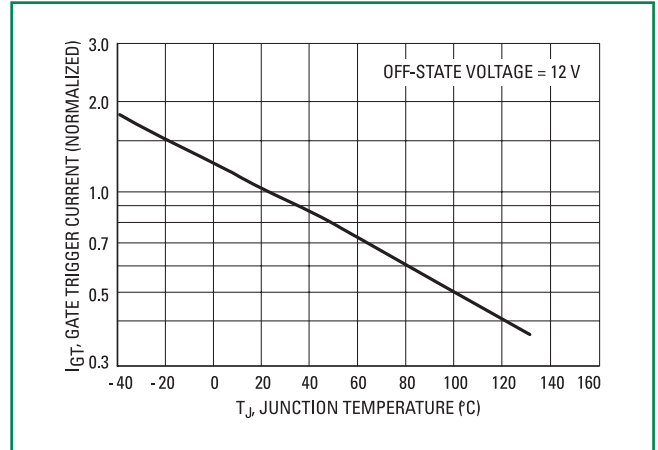


Figure 8. Typical Gate Trigger Voltage vs. Temperature

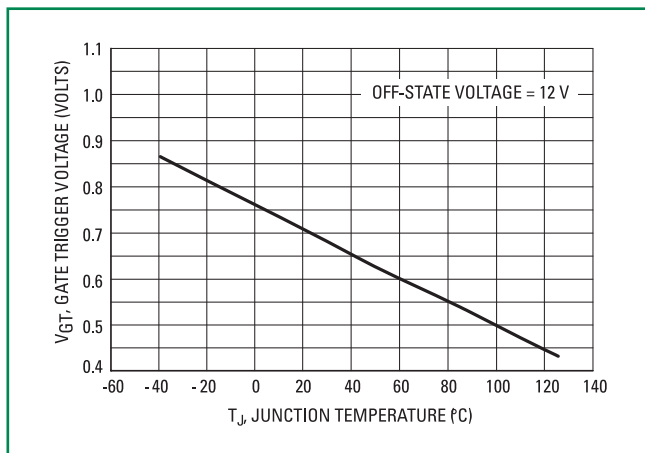
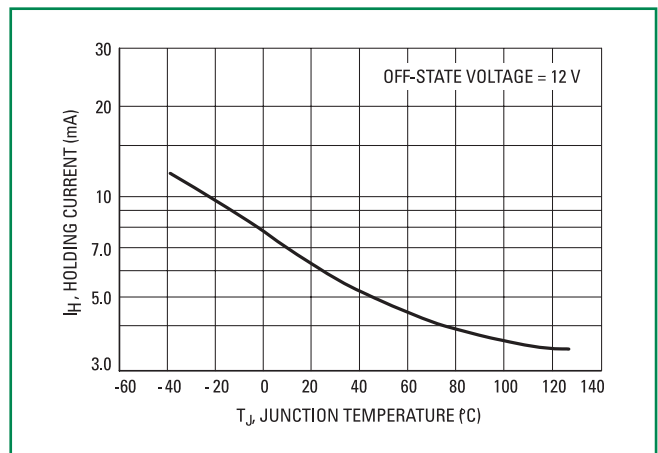
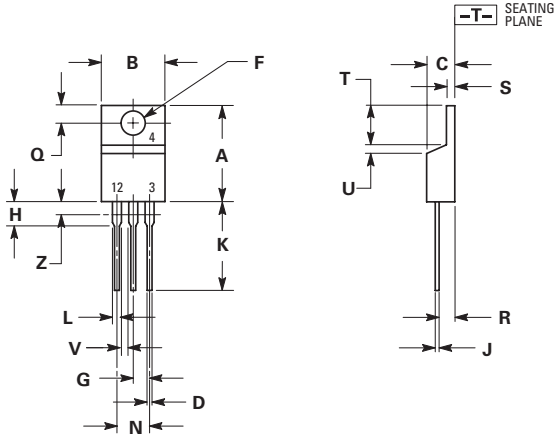


Figure 9. Typical Holding Current vs. Temperature



Dimensions

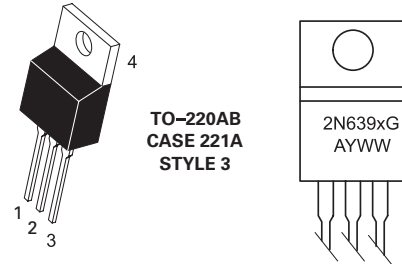


Dim	Inches		Millimeters	
	Min	Max	Min	Max
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

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Part Marking System



TO-220AB
CASE 221A
STYLE 3

2N639x = Device Code
x = 4, 5, 7, or 9
G = Pb-Free Package
A = Assembly Location
Y = Year
WW = Work Week

Pin Assignment

1	Cathode
2	Anode
3	Gate
4	Anode

Ordering Information

Device	Package	Shipping
2N6394G	TO-220AB (Pb-Free)	500 Units / Box
2N6394TG		50 Units / Box
2N6395G		500 Units / Box
2N6397G		500 Units / Box
2N6397TG		50 Units / Box
2N6399G		500 Units / Box
2N6399TG		50 Units / Box

Mouser Electronics

Authorized Distributor

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